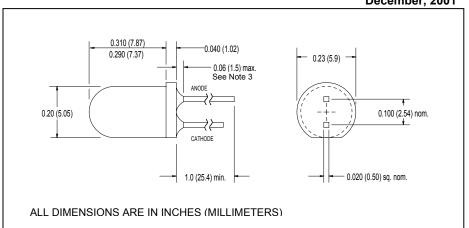
CLD370F Plastic PIN Photodiode



December, 2001





features

- · fast switching speed
- low junction capacitance
- 850 nm peak response
- large photosensitive area
- · sharp cutoff to visible wavelengths
- ± 30° acceptance angle

description

The CLD370F is a high gain silicon photodiode mounted in a T-1¾ (5mm) dark plastic package. The chip has an active area of approximately 0.080" x 0.080" (4 square mm) and is intended for use as an infrared sensor. The dark tinting of the package effectively attenuates wavelengths shorter than 700nm eliminating most visible light interference.

absolute maximum ratings (T_A = 25°C unless otherwise stated)

storage temperature	40°C to +125°C
operating temperature	
lead soldering temperature ⁽¹⁾	260°C
continuous power dissipation ⁽²⁾	150mW

notes:

- 1. 0.06" (1.5mm) from the header for 5 seconds maximum
- 2. Derate linearly 1.6mW/°C from 25°C free air temperature to $T_A = +100$ °C.
- 3. Protruding resin under flange is 0.06" (1.5mm) max.

symbol	parameter	min	typ	max	units	test conditions
Isc	Short-circuit current ⁽¹⁾	5.0 -	10.0 60.0	-: -	μ Α μ Α	$V_R = 5V, E_e = 0.1 \text{mW/cm}^2$ $V_R = 5V, E_e = 1.0 \text{mW/cm}^2$
I _D	Dark current	-	-	30	nA	V _R = 10V, E _e = 0
V_{BR}	Reverse breakdown	30	-	-	V	$I_R = 100 \mu A, E_e = 0$
СЈ	Junction capacitance	-	25	-	pF	$V_R = 3V, E_e = 0. f = 1MHz$
Vo	Open circuit voltage	-	350	-	mV	$E_e = 0.1 \text{mW/cm}^2$
Θ_{HP}	Total angle at half sensitivity points	-	60	-	deg.	
t _r , t _f	Output rise and fall time ⁽¹⁾	-	30	-	ns	$R_L = 1k\Omega$, $V_R = 10V$

Note: 1. Radiation source is an aluminum gallium arsenide IRED operating at a peak wavelength of 850nm.

Clairex reserves the right to make changes at any time to improve design and to provide the best possible product.

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